



Eldad Bahat-Treidel (Autor)

# GaN-Based HEMTs for High Voltage Operation: Design, Technology and Characterization



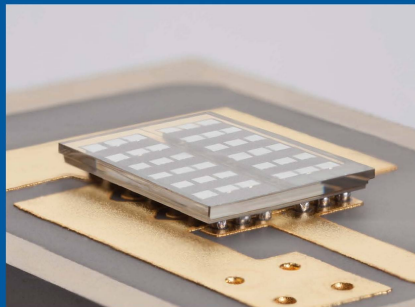
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GaN-Based HEMTs for High Voltage  
Operation: Design, Technology and  
Characterization



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